

Description

The AU1201P0 is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AU1201P0 complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into an ultra-small 0.6x0.6x0.3mm lead-free DFN package. The small size and high ESD surge protection make AU1201P0 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Ultra small package: 0.6x0.6x0.3mm
- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 12V
- Low clamping voltage
- 2-Pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±30kV
 Contact discharge: ±30kV
 - IEC61000-4-5 (Lightning) 3.5A (8/20µs)
- RoHS Compliant

Mechanical Characteristics

- Package: DFN0603-2 (0.6×0.3×0.3mm)
- Case Material: "Green" Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

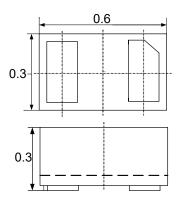
- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, LCD Displays

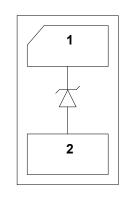
Marking Information



BZ = Device Marking Code Bar denotes Pin1

Dimensions and Pin Configuration





Package Dimensions

Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size	
AU1201P0	10000/Tape & Reel	7 inch	



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

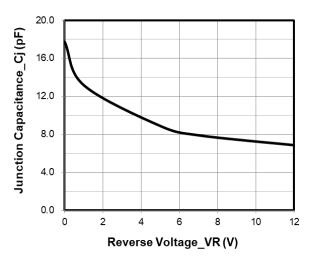
Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20µs)	Ppk	70	W	
Peak Pulse Current (8/20µs)	Ipp	3.5	Α	
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV	
ESD per IEC 61000-4-2 (Contact)	VESD	±30		
Operating Temperature Range	TJ	-55 to +125	°C	
Storage Temperature Range	Tstg	−55 to +150	°C	

Electrical Characteristics (T_A=25°C unless otherwise specified)

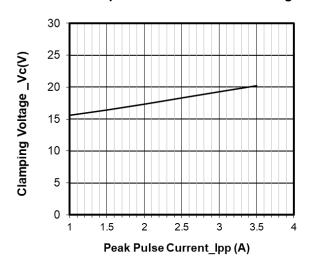
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			12	V	Pin 1 to Pin 2
Breakdown Voltage	VBR	13.3			V	IT = 1mA, Pin 1 to Pin 2
Reverse Leakage Current	I _R			0.2	μA	VRWM = 12V, Pin 1 to Pin 2
Forward Voltage	VF		0.8	1.2	V	IF = 10mA, Pin 2 to Pin 1
Clamping Voltage	Vc			20	V	IPP = 3.5A (8 x 20µs pulse), Pin 1 to Pin 2
Junction Capacitance	Cl		18	20	pF	VR = 0V, f = 1MHz



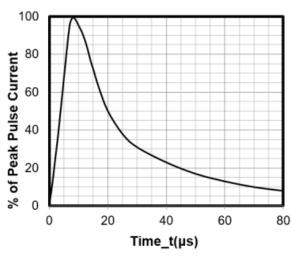
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



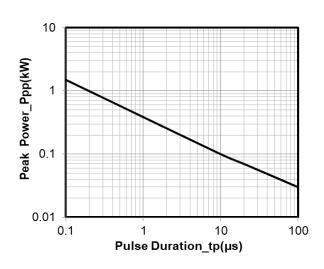
Junction Capacitance vs. Reverse Voltage



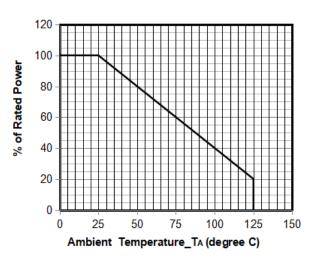
Clamping Voltage vs. Peak Pulse Current



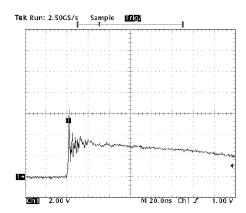
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



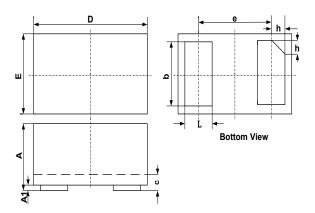
Power Derating Curve



Note: Data is taken with a 10x attenuator
ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

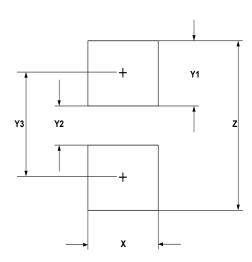


DFN0603-2 Package Outline Drawing



	DIMENSIONS			
	MILLIMETERS			
SYM	MIN	NOM		MAX
Α	0.230			0.330
A1	0.000	0.020		0.050
b	0.215	0.245		0.275
С	0.120	0.150		0.180
D	0.550	0.600		0.650
е	0.355 BSC			
Е	0.250	0.300		0.350
L	0.160	0.190		0.220
h	0.079 BSC			

Suggested Land Pattern



SYM	DIMENSIONS				
STIVI	MILLIMETERS	INCHES			
Х	0.30	0.012			
Y1	0.25	0.010			
Y2	0.15	0.006			
Y3	0.40	0.016			
Z	0.65	0.026			

Contact Information

Applied Power Microelectronics Inc.

Website: http://www.appliedpowermicro.com

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606

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